

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprising an active area of a MOSFET which is separated by an element isolation area on a semiconductor substrate, at least one gate electrode provided over the active area, and at least one source/drain contact formed on a surface of the active area at one side of the gate electrode, wherein the gate electrode has a shape to vary so that a gate length decreases with increasing a distance from a position of the source/drain contact along the gate electrode.